

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	207	(recrystallized near polysilicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 16:52
L2	11	(recrystallized near polysilicon) with capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 16:52
L3	11	(recrystallized near polysilicon) near10 capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 16:53
L4	0	((recrystallized near polysilicon) near10 capacitor).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 16:53
L5	0	((recrystallized near polysilicon) with capacitor).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 16:53
L6	22	((recrystallized near polysilicon)). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 16:53
L7	98356	((recrystallized near polysilicon)). clm. anc capacitor.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 16:53
L8	1	((recrystallized near polysilicon)). clm. and capacitor.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 16:54
L9	1	((recrystallized near polysilicon)). clm. and capacitor.clm. and silicide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 16:54

L10	1	((recrystallized near polysilicon)). clm. and capacitor.clm. and silicide.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 16:55
L11	1	((recrystallized near polysilicon)) and capacitor.clm. and silicide.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 16:55
L12	6	((recrystallized near polysilicon)) and capacitor and silicide.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 16:55
L13	25	((recrystallized near polysilicon)) and capacitor and silicide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 16:55
L14	0	((recrystallized near polysilicon)) same capacitor same silicide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 16:55
L15	25	((recrystallized near (poly or polysilicon))) and capacitor and silicide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 16:55
L16	25	((recrystallized near (poly or polysilicon))) and capacitor and silicide and gate and electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 16:59
L17	28	((recrystallized near (poly or polysilicon))) and (capacitor near5 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 16:59
L18	12	((recrystallized near (poly or polysilicon))) and (capacitor near5 electrode) and silicide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 17:03
L19	8822	(electrode near5 silicide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 17:03

L20	9	(electrode near5 silicide) and (recrystallized near polysilicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 17:05
L21	1	(electrode near2 silicide) and (recrystallized near polysilicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 17:05
L22	0	(electrode near2 silicide) and (recrystallized near polysilicon) and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 17:05
L23	5	(electrode near5 silicide) and (recrystallized near polysilicon) and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 17:06
L24	55	(recrystallized near polysilicon) and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 17:06
L25	25	(recrystallized near polysilicon) and capacitor and electrode and silicide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 17:06
L26	5	(recrystallized near polysilicon) and capacitor and (electrode near10 silicide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 17:07
L27	30	((recrystallized or crystallized or recrystal or crystal) near polysilicon) and capacitor and (electrode near10 silicide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 17:07
L28	52	((recrystallized or crystallized or recrystal or crystal) near (poly or polysilicon)) and capacitor and (electrode near10 silicide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 17:10
L29	5	((recrystallized or crystallized or recrystal or crystal) near (poly or polysilicon)) same capacitor and (electrode near10 silicide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 17:08

L30	1	((recrystallized or crystallized or recrystal or crystal) near (poly or polysilicon)) same capacitor same (electrode near10 silicide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 17:08
L31	24	((recrystallized or crystallized) near (poly or polysilicon)) and capacitor and (electrode near10 silicide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 17:10
L32	0	((recrystallized or crystallized) near (poly or polysilicon)) with capacitor and (electrode near10 silicide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 17:10
L33	0	((recrystallized or crystallized) near (poly or polysilicon)) with capacitor with (electrode near10 silicide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 17:10
L34	12	((recrystallized or crystallized) near (poly or polysilicon)) with capacitor with (electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 17:10
L35	10	((recrystallized) near (poly or polysilicon)) with capacitor with (electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 17:11
L36	6	((recrystallized) near (poly or polysilicon)) near10 capacitor with (electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 17:11
L37	6	((recrystallized) near (poly or polysilicon)) near10 capacitor near10 (electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 17:11